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Application Note

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Using MC68HC908 On-Chip FLASH Programming Routines

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1 Introduction

In this application note, the following devices are supported:

MC68HC908EY16
MC68HC908GR4
MC68HC908GR4A
MC68HC908GR8
MC68HC908GR8A
MC68HC908GT16
MC68HC908JB8
MC68HC908JK1
MC68HRC908JK1
MC68HLC908JK1
MC68HC908JK1E
MC68HRC908JK1E
MC68HLC908JK1E
MC68HC908JK3
MC68HRC908JK3
MC68HLC908JK3
MC68HC908JK3E
MC68HRC908JK3E
MC68HLC908JK3E
MC68HC908JL3

MC68HLC908JL3 MC68HC908JL3E MC68HRC908JL3E MC68HLC908JL3E MC68HC908KX2 MC68HC908KX8 MC68HC908QT1 MC68HC908QT2 MC68HC908QT4 MC68HC908QY1 MC68HC908QY2 MC68HC908QY4 MC68HLC908QT1 MC68HLC908QT2 MC68HLC908QT4 MC68HLC908QY1 MC68HLC908QY2 MC68HLC908QY4

MC68HRC908JL3

Table of Contents

1	Intro	oduction				
2	Pag	e Erase Issue 2				
3	The	Routines				
	3.1	GETBYTE				
	3.2	RDVRRNG				
	3.3	PRGRNGE				
	3.4	ERARNGE — Page Erase 5				
	3.5	ERARNGE — Mass Erase 6				
	3.6	DELNUS				
4	Dev	rice-Specific Information Related to				
	On-	chip FLASH Routines 8				
5	V	ariables				
6		Data Structure				
7	Add	Iresses of Routines 10				
8	MC	68HC908KX8 Trim Routine				
9	Тур	ical Routine Calls 10				
	9.1	Example for GETBYTE 11				
	9.2	Examples for RDVRRNG 11				
	9.3	Example for Page Erase Operation 12				
	9.4	Examples for Mass Erase Operation 12				
	9.5	Examples for PRGRNGE 13				
	9.6	Example for DELNUS 14				
10	Pag	e Erase Workaround 14				
11	ROM Routines Source Code 15					
12	Workaround Code 29					



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Page Erase Issue

The original purpose of this application note was to describe how to use the on-chip FLASH routines residing in ROM (read-only memory). In the first version of the note, only a few devices were supported.

This updated application note not only supports the original purpose but also accomplishes the following purposes:

- 1. There is a bug on the page erase operation using the on-chip FLASH erase routine described in the original note. In this note, the bug is described and its workaround is provided. For details, refer to Section 2, "Page Erase Issue."
- 2. More devices that have the on-chip FLASH routines are supported.
- 3. Information is updated to provide additional useful information to the user.

2 Page Erase Issue

The page erase issue does not apply to all devices supported in this note. The issue applies to the following devices:

MC68HC908GR4	MC68HC908GR4A	MC68HC908GR8	MC68HC908GR8A	MC68HC908JB8
MC68HC908JK1	MC68HRC908JK1	MC68HLC908JK1	MC68HC908JK1E	MC68HRC908JK1E
MC68HLC908JK1E	MC68HC908JK3	MC68HRC908JK3	MC68HLC908JK3	MC68HC908JK3E
MC68HRC908JK3E	MC68HLC908JK3E	MC68HC908JL3	MC68HRC908JL3	MC68HLC908JL3
MC68HC908JL3E	MC68HRC908JL3E	MC68HLC908JL3E	MC68HC908KX2	MC68HC908KX8

If the user target device is not one of the above, skip this section. The device does not have the page erase issue.

One of the on-chip FLASH routines, named ERARNGE, supports FLASH erase and was meant to erase a page size of FLASH or the whole FLASH array.

ERARNGE works properly when the mass erase operation is performed. However, we found that ERARNGE does not fully erase a selected page when a page erase operation is performed. Furthermore, it has the potential to erase a vector page unintentionally.

The issue is caused by servicing the computer operating properly (COP) during the t_{Erase} delay routine. The workarounds for this issue are:

- 1. Write your own page erase routine and keep it in FLASH. Whenever a page erase is desired, copy the routine to RAM and execute the erase from there. Be sure to omit instructions that service the COP.
- 2. Refer to Section 10, "Page Erase Workaround." In the workaround, ERARNGE located in ROM is used so that the user does not need to develop his/her own routine. The new page erase routine is called in a similar manner to the original. However, additional RAM is required to perform this routine.

3 The Routines

The collection consists of five callable routines, which are described in Table 2. These routines are explained briefly here, but the parameters and the passing method are addressed in later sections.





3.1 GETBYTE

GETBYTE is a routine that receives a byte on the monitor mode communication port defined for that particular device, and this received value is passed back to the calling routine in the accumulator. For these devices, the communication port is either port A0 or port B0. Table 3 shows which communication port (COMMPORT) is used for each device.

GETBYTE expects the same non-return-to-zero (NRZ) communication protocol and baud rate that is used in monitor mode. The difference between this routine's method of receiving a byte and when the monitor receives a byte is that the monitor echoes back whatever is received. It may be more efficient for a RAM program to use this routine when receiving data from a host to eliminate the time overhead in sending out every byte that is received. This is especially true if the host program and RAM routine already have a built-in error detection scheme, such as a message checksum, and there might not be a need to do an echo check for each byte sent.

This routine detects a framing error when a STOP bit is not detected. If the carry (C) bit of the condition code register (CCR) is cleared after returning from this routine, a framing error occurred during the data receiving process. Therefore, the data in the accumulator is not reliable. The user software is responsible for handing such errors.

The communication baud rate is defined by the internal operating bus frequency (f_{op}) divided by a constant value. Table 1 shows the divider value and a typical baud rate for each device.

	Divider Value	Typical Baud Rate
MC68HC908EY16	256	9600bps @ f _{op} =2.4576MHz
MC68HC908GR4/8(A)	256	9600bps @ f _{op} =2.4576MHz
MC68HC908GT16	256	9600bps @ f _{op} =2.4576MHz
MC68HC908JB8	306	9600bps @ f _{op} =3MHz
MC68H(R/L)C908JL1(E) MC68H(R/L)C908JK1(E)M C68H(R/L)C908JK3(E)	256	9600bps @ f _{op} =2.4576MHz
MC68HC908KX2/8	256	9600bps @ f _{op} =2.4576MHz
MC68HC908QT1/2/4 MC68HC908QY1/2/4	256	9600bps @ f _{op} =2.4576MHz
MC68HLC908QT1/2/4 MC68HLC908QY1/2/4	256	9600bps @ f _{op} =2.4576MHz when ECGST bit in OSCSTAT is set
	208	4800bps @ f _{op} =1MHz when ECGST bit in OSCSTAT is cleared

Table 1. Communication Baud Rate



The Routines

For the MC68HLC908QT/QYxx devices, the divider value depends on the status of the external clock status (ECGST) bit in the oscillator status (OSCSTAT) register. When this bit is set, the divider value of 256 is selected. And when this bit is cleared, the divider value of 208 is selected.

To use GETBYTE, the COMMPORT pin must have an external pull-up.

Interrupts are not masked (the I bit is not set) and the COP is not serviced in this routine. User software should ensure that interrupts are blocked during character reception.

3.2 RDVRRNG

RDVRRNG routine serves two purposes:

- Send-Out Option Used to read a range of FLASH locations and to send the read data through COMMPORT.
- Verify Option Used to read a range of FLASH locations and to verify the read data against DATA array.

3.2.1 Send-Out Option

If the accumulator is initialized with \$00 when entering RDVRRNG, then the data read will be sent to the monitor mode communication port (COMMPORT). Therefore, the communication baud rate is the same as the baud rate described in Section 3.1, "GETBYTE." When this option is selected, the COMMPORT pin must be pulled up and configured as an input and the communication data bit must be initialized to 0.

3.2.2 Verify Option

If the accumulator is initialized with a non-zero value, the read data is verified against the DATA array for each byte of FLASH, and the DATA array is replaced by the data read from FLASH. The carry (C) bit of the condition code register (CCR) is set if the data in the specified range is verified successfully against the data in the DATA array.

Both options calculate a checksum on data read in the range. This checksum, which is the LSB of the sum of all bytes in the entire data collection, is stored in the accumulator upon return from the function.

To select a range, the beginning and end of the FLASH range to be read are specified as parameters to FADDR and LADDR. These parameters are explained in more detail later in Section 5, "Variables."

Interrupts are not masked. COP is serviced in RDVRRNG. However, the COP timeout might still occur in the send-out option if COP is configured for a short timeout period.

3.3 PRGRNGE

PRGRNGE is used to program a range of FLASH locations with data loaded into the DATA array. As with RDVRRNG, the start and end location of the range of addresses to be programmed is passed by parameters called FADDR and LADDR, respectively. A check to see that all bytes in the specified range are erased is not performed by this routine prior to programming. Nor does this routine do a verification after programming, so there is no return confirmation that programming was successful. This routine can be



used in conjunction with RDVRRNG to perform a complete program and verification cycle of the specified range.

PRGRNGE allows any range to be passed to it. That is, the range does not have to be coincident with row boundaries¹. The range specified can be at the beginning of a row, the middle of a row, the end of a row, or it can be a range overlapping row boundaries. The user must ensure only two things:

- The range specified is first erased
- The data for the specified range must be in the data array in RAM

Because this routine calls the delay routine DELNUS to generate proper delays, parameter CPUSPD must be set correctly when calling PRGRNGE. Parameters required for this routine are explained in more detail later in Section 5, "Variables."

Interrupts are masked (the I bit is set) and COP is serviced in this routine.

NOTE

Regarding the JB8 and JL/JKxx(E), the FLASH block protect register (FLBPR) dose not consist of FLASH. Since FLASH is always protected after reset, unprotect the locations to be programmed in the user software before calling this routine.

3.4 ERARNGE — Page Erase

The page erase operation using the ERARNGE routine supports the following devices:

MC68HC908EY16	MC68HC908GT16	MC68HC908QT1	MC68HC908QT2	MC68HC908QT4
MC68HC908QY1	MC68HC908QY2	MC68HC908QY4	MC68HLC908QT1	MC68HLC908QT2
MC68HLC908QT4	MC68HLC908QY1	MC68HLC908QY2	MC68HLC908QY4	

If the user target device is not in the above list, refer to Section 2, "Page Erase Issue."

ERARNGE can be called to erase a page of FLASH. This routine does not use the last address (LADDR) variable. The first address (FADDR) placed in H:X in the two previous routines actually can be any address within a page to be erased. To select the page erase operation, a control variable in RAM called CTRLBYT is used. Writing \$00 to CTRLBYT selects the page erase operation. To set proper delays, CPUSPD must be set correctly. CPUSPD and CTRLBYT are explained in more detail later in Section 5, "Variables."

Interrupts are masked. In the EY16 and GT16 ERARNGE, COP is not serviced. On the other hand in the QT/QYxx ERARNGE, COP is serviced. Servicing COP does not cause the page erase issue for these devices.

Regarding the MC68HLC908QT/QYxx devices, only 1 MHz operating frequency (f_{op}) is supported so that CPUSPD must be set with a value \$04.

^{1.} The flexible boundary condition does not apply for the MC68HLC908QT/QYxx devices. When FLASH is programmed using this routine for these devices, all bytes that will be programmed must be in the same row. Furthermore, only a 1 MHz operating frequency (f_{op}) is supported so that CPUSPD must be set with a value \$04. COP is not serviced.



NOTE

Regarding the EY16 and GT16, t_{Erase} delay is set with 1ms in the page erase operation using this routine. Therefore, this setup supports less than 1000 program/erase cycles. On the other hand the QT/QYxx ERARNGE uses t_{Erase} delay 4ms in this routine. This setup supports more than 1000 program/erase cycles.

3.5 ERARNGE — Mass Erase

All devices listed in this note can use ERARNGE to execute the mass erase operation.

ERARNGE can be called to erase the entire FLASH. This routine does not use the last address (LADDR) variable. The first address (FADDR) placed in H:X can be any address within the FLASH. To select a mass erase operation, a control variable in RAM called CTRLBYT is used. Writing \$40 to CTRLBYT selects the mass erase operation. To set the proper delay, CPUSPD must be set correctly. CPUSPD and CTRLBYT are explained in more detail later in Section 5, "Variables."

Regarding the MC68HLC908QT/QYxx devices, only 1 MHz operating frequency (f_{op}) is supported so that CPUSPD must be set with a value \$04.

interrupts are masked. In the EY16 and GT16 ERARNGE, COP is not serviced. In the QT/QYxx ERARNGE, COP is serviced.

NOTE

Regarding the JB8 and JL/JKxx(E), the FLASH block protect register (FLBPR) does not consist of FLASH. Since FLASH is always protected after reset, unprotect the whole FLASH array in the user software before calling this routine.

3.6 DELNUS

DELNUS is a delay routine used in support of PRGRNGE and ERARNGE. It can, however, be called independently in the user software. DELNUS uses two parameters stored in the accumulator (A) and the X register (X). Neither of these parameters is passed as an absolute value. The total delay (cycles) resulting from this routine is:

 $DELNUS = 3 \times (A \text{ value}) \times (X \text{ value}) + 8 \text{ cycles}$

where a value of A is 4 or greater and a value of X is 1 or greater. In PRGRNGE and ERARNGE, the CPUSPD value (which is frequency parameter) is loaded into A.

Because this routine is called from a jump table, three additional cycles are included in the above equation.

Interrupts are not masked and COP is not serviced in DELNUS.



	GETBYTE	RDVRRNG	PRGRNGE	Page Erase ERARNGE ¹	Mass Erase ERARNGE	DELNUS
Routine Description	Gets a byte of data from COMMPORT	Reads and/or verifies a range of locations	Programs a range of locations	Erases a page	Erases the entire array	Generates delay $3 \times A \times X + 8$ (cycles)
Hardware Requirement	Pullup on COMMPORT pin	Pullup on COMMPORT pin	N/A	N/A	N/A	N/A
Entry Conditions	COMMPORT direction is configured as input	H:X contains first address of range LADDR contains last address read A contains option selection, A=\$00 for send-out option; A \neq \$00 for verify option For send-out option, COMMPORT input and 0 data bit (DDRx0=0, PTx0=0) For verify option, DATA contains data against which to compare read data	LADDR contains last address to	H:X contains address within a page to be erased CTRLBYT contains \$00 CPUSPD contains 4 * f _{op}	H:X contains address within an array to be erased CTRLBYT contains \$40 CPUSPD contains 4 * f _{op}	A contains value between 4 and 255 X contains value between 1 and 255
Exit Conditions	A is loaded with byte received C bit indicates framing error (error:C=0)	C bit is set if good compare; A contains checksum DATA contain read FLASH data (verify option)			Preserves contents of H:X (address passed)	
l Bit	_	_		I bit is set	I bit is set	_
СОР	Not Serviced	Not Serviced	Serviced except HLC908QT/QY	EY16 and GT16: Not serviced QT/QYxx: Serviced	EY16 and GT16: Not serviced QT/QYxx: Serviced	Not Serviced
Subroutines Called	_		DELNUS	DELNUS	DELNUS	_
Variables Read		LADDR, DATA	LADDR, DATA, CPUSPD	CTRLBYT, CPUSPD	CTRLBYT, CPUSPD	
Variables Modified		DATA				
Stack Used	4 bytes	6 bytes	7 bytes	5 bytes	5 bytes	3 bytes

Table 2. On-Chip FLASH Routines

NOTES:

Before using this routine, confirm that this routine supports the user target device (Refer to Section 2, "Page Erase Issue").



4 Device-Specific Information Related to On-chip FLASH Routines

Table 3 shows the useful information for each device when the on-chip FLASH routines are used.

	RAM	ROWSIZ	COMMPORT	FLBPR	Put_Byte
MC68HC908EY16	\$40	32	PTA0	\$FF7E	_
MC68HC908GR4/8(A)	\$40	32	PTA0	\$FF7E	\$FEAA
MC68HC908GT16	\$40	32	PTA0	\$FF7E	
MC68HC908JB8	\$40	64	PTA0	\$FE09 ¹	\$FED6
MC68H(R/L)C908JK1(E) MC68H(R/L)C908JK3E) MC68H(R/L)C908JL3(E)	\$80	32	PTB0	\$FE09 ⁽¹⁾	\$FED0
MC68HC908KX2/8	\$40	32	PTA0	\$FF7E	\$FEAA
MC68HC908QT1/2/4 MC68HC908QY1//2/4	\$80	32	PTA0	\$FFBE	\$FEA1
MC68HLC908QT1/2/4 MC68HLC908QY1/2/4	\$80	32	PTA0	\$FFBE	\$FE9F

Table 3. Device-Specific Information

NOTES:

FLBPR does not consist of FLASH. Unprotect the FLASH before programming or erasing.

In Table 3, RAM indicates the RAM start address. ROWSIZ indicates the size of a FLASH row. COMMPORT indicates a communication port for the monitor mode. FLBPR indicates FLASH block protect register address. Put_Byte indicates the address of the routine to send a byte through the communication port (COMMPORT). The communication baud rate is the same as the baud rate described in Section 3.1, "GETBYTE." However, this routine is not officially supported. Therefore, the address might be changed in the future without any notice. We recommend that users develop their own Put_Byte routines.

5 Variables

Table 4 shows the variables used in the routines. These variables are either passed in a register or as static variables in a predefined location in RAM. FADDR is a 2-byte value that represents the first address in the range on which to be operated. It is passed in the H:X registers when a call is made to one of the routines. The first address of a range can be any valid FLASH address and does not have to be on a row or page boundary.

LADDR is the last address in the range and is passed in the first byte of the data structure in RAM. This data structure is very simple, consisting of the last address, the CPU speed variable, a control byte, and the



data array. It is discussed in detail in Section 6, "The Data Structure." The last address, like the first address, can be any valid FLASH address and is not restricted to being the last byte of a page or row.

The internal operating bus frequency (f_{op}) of the device on which the FLASH operation is to be performed is passed in a variable called CPUSPD. It is a 1-byte value which is passed in the data structure and should be given as the rounded product of four times the actual internal operating (bus) frequency, such that if f_{op} is 2.4576 MHz, then the value passed should be decimal 10 (\$0A). This variable is used to normalize the length of delays with respect to the operating frequency, and passing a value four times the actual frequency provides better resolution.

The remaining operating parameter used in these routines is the control byte (CTRLBYT). Value \$40 is set in this byte when calling ERARNGE to perform a mass erase. If ERARNGE is called with the intention of performing a page erase, then value \$00 must be set.

Variable Name	Description	Size	Location/Passing Method
FADDR	First address of range of locations	2 bytes	H:X
LADDR	Last address of range of locations	2 bytes	Data structure
CPUSPD	$4 \times f_{op}$	1 byte	Data structure
CTRLBYT	Mass bit (bit 6)	1 byte	Data structure
DATA	Data array	Variable	Data structure

Table 4. Variables Used in Routines

6 The Data Structure

The data structure is a collection of static variables in RAM used in the execution of the three main routines: PRGRNGE, ERARNGE, and RDVRRNG. The data structure is in the same relative location in RAM and the content is the same data and order for all of the devices containing these ROM routines. The structure always starts in the ninth byte of RAM and the order of the variables is as shown in Table 5.

Table 5. Data Structure	Location and Content
-------------------------	----------------------

Location	Variable Name	Size	Description
RAM + \$08	CTRLBYT	1 byte	Control byte setting erase size
RAM + \$09	CPUSPD	1 byte	CPU speed passed as $4 \times f_{op}$
RAM + \$0A RAM + \$0B	LADDR	2 bytes	Last address for read a range and program a range
RAM + \$0C	DATA	Variable	Variable number of bytes of passed data for programming or verifying a block



Addresses of Routines

Note that the data array DATA is variable in length. This is done to support a variable number of locations on which to perform any of the programming, reading, or verifying actions. Most of the time, these actions will be performed on a row of data at one time, although that need not be the case. Some of these devices have a rather small RAM array, and the size of the data array must be limited to the size of RAM minus the stack needed and the size of any RAM routine being executed. If the RAM routine is kept to a reasonable size, then there should not be a problem defining the data array to be the size of a row for any of the devices in this collection.

7 Addresses of Routines

The address to call each of the five routines varies among the devices. Table 6 gives the absolute address that should be used when calling the routines.

	GETBYTE	RDVRRNG	ERARNGE	PRGRNGE	DELNUS
MC68HC908EY16	\$1000	\$1003	\$1006	\$1009	\$100C
MC68HC908GR4(A) MC68C908GR8(A)	\$1C99	\$1CAD	\$1DA0 ¹	\$1CEC	\$1D96
MC68HC908GT16	\$1B50	\$1B53	\$1B56	\$1B59	\$1B5C
MC68HC908JB8	\$FC00	\$FC03	\$FC06 ⁽¹⁾	\$FC09	\$FC0C
MC68HC908JL1(E) MC68HC908JK3(E)	\$FC00	\$FC03	\$FC06 ⁽¹⁾	\$FC09	\$FC0C
MC68HC908KX2 MC68HC908KX8	\$1000	\$1003	\$1006 ⁽¹⁾	\$1009	\$100C
MC68HC908QT1/2/4 MC68HC908QY1/2/4	\$2800	\$2803	\$2806	\$2809	\$280C
MC68HLC908QT1/2/4 MC68HLC908QY1/2/4	\$2800	\$2803	\$2806	\$2809	\$280C

Table 6. Addresses of Routines

NOTES:

¹ This routine is used only for the mass erase operation.

8 MC68HC908KX8 Trim Routine

The MC68HC908KX8 Trim routine was supported in the original note. However, because another application note, AN2312, describes a more accurate trim method, this section was removed in this document.

9 Typical Routine Calls

This section provides examples of how the on-chip FLASH routines may be called.



9.1 Example for GETBYTE

To call GETBYTE to receive a byte of data on the communication port, the only thing that needs to be done is to ensure that the communication port is configured as an input and has a pullup.

```
GETBYTE: equ $2800 ;QY4 GETBYTE jump address
bclr 0,DDRA0 ;Configure port A bit 0 as an input
jsr GETBYTE ;Call GETBYTE routine
bcc FrameError ;If C bit is clear, framing error
; occurred. Take a proper action
```

9.2 Examples for RDVRRNG

This example calls the RDVRRNG routine to use the send-out option. In this example, a range of FLASH from \$F000 to \$F010 is read and read data is sent out through COMMPORT.

RDVRRNG:	equ	\$2803	;QY4 RDVRRNG jump address
	ldhx sthx	0,PTA #\$F010 LADDR #\$F000	<pre>;Initialize data bit to zero PTA0=0 ;Load last address of range to ; LADDR ;Load beginning address of range ; to H:X</pre>
	clra jsr	RDVRRNG	;A=0 to select send-out option ;Call RDVRRNG routine ; A contains a checksum value

The next example also uses the RDVRRNG. In this example, the verify option is selected. A range of FLASH from \$E800 to \$E81F is read and the read data is verified against data in the DATA array in RAM. When the verify is successful, the C bit in the CCR gets set.

RDVRRNG:	equ	\$2803	;QY4 RDVRRNG jump address
Data_load:	ldhx lda	#\$0000 #\$AA	;Index offset into DATA array ;Initial data value to store in array
	coma		
	sta	DATA, x	;Fill DATA array, 32 bytes data, ; to verify against programmed FLASH
	aix	#1	; data (In this example verifying data
	cphx	#\$20	; is \$55, \$AA, \$55, \$AA)
	bne	Data_load	
	ldhx	#\$E81F	;Load last address of range to
	sthx	LADDR	; LADDR
	ldhx	#\$E800	;Load beginning address of range ; to H:X
	lda	#\$55	;Write non-zero value to A to select



Typical Routine Calls

		; the verify option
jsr	RDVRRNG	;Call RDVRRNG routine
bcc	Error	; If bit C is cleared, verify failed
		; Take a proper action
		; A contains a checksum value

9.3 Example for Page Erase Operation

Before taking a look at this example, refer to Section 3.4, "ERARNGE — Page Erase," to confirm that this operation is supported for the user target device.

This example performs the page erase operation using ERARNGE. The variable CPUSPD is set to a value which reflects an 8 MHz operating frequency, that is $4f_{op} = 4 \times 8 = 32$ (\$20). CTRLBYT must be loaded with \$00 to select the page erase operation. To erase a page from \$EE00 to \$EE3F, an address within this page must be loaded into H:X. Note that the FLASH block protect register must not be protecting the page.

Regarding the HLC908QT/QYxx devices, note that only $f_{op} = 1$ MHz is supported.

ERARNGE: equ \$2806 ;QY4 ERARNGE jump address
mov #\$20,CPUSPD ;fop = 8MHz in this example
mov #\$00,CTRLBYT ;Select Page erase operation
ldhx #\$EE01 ;Load any address within the
; page to H:X
jsr ERARNGE ;Call ERARNGE routine

9.4 Examples for Mass Erase Operation

This example performs the mass erase operation using the ERARNGE routine. CPUSPD is set to a value which reflects a 6 MHz operating frequency, that is $4f_{op} = 4 \times 6 = 24$ (\$18). CTRLBYT must be loaded with \$40 to select the mass erase operation. Any valid FLASH address is loaded into H:X when doing a mass erase. Note that the mass erase operation will not be successful if the FLASH block protect register has any block protected.

Regarding the HLC908QT/QYxx devices, note that only $f_{op} = 1$ MHz is supported.

ERARNGE: equ \$2806 ;QY4 ERARNGE jump address mov #\$18,CPUSPD ;fop = 6 MHz in this example mov #\$40,CTRLBYT ;Select Mass erase operation ldhx #\$F000 ;Load any address within the ; page to H:X jsr ERARNGE ;Call ERARNGE routine

Regarding the JB8 and JL/JKxx(E) devices, FLBPR does not consist of FLASH. Because FLASH is always protected after reset, unprotect the entire FLASH array in user software before calling this routine.



9.5 Examples for PRGRNGE

The first example shows how to program one full row. The variable CPUSPD is set to a value which reflects an 2.4576 MHz operating frequency, that is $4f_{op} = 4 \times 2.4576 = 10$ (\$0A). In this example, the target device is the MC68HC908QY4.

Regarding the HLC908QT/QYxx devices, note that only $f_{op} = 1$ MHz is supported.

```
PRGRNGE:
                  $2809
                              ;QY4 PRGRNGE jump address
            equ
                  #$0000
            ldhx
                              ; Index offset into DATA array
                              ;Initial data value (inverted)
            lda
                  #$AA
Data_load:
            coma
                              ;Alternate between $55 and $AA
            sta
                  DATA,x
                              ;Fill DATA array, 32 bytes data,
                              ; values to program into FLASH
                              ; (ie. 55, AA, 55, AA....)
            aix
                  #1
            cphx
                 #$20
                  Data_load
            bne
                  #$0A,CPUSPD ; fop = 2.4576 MHz in this example
            mov
            ldhx #$EE1F
                             ;Load last address of the row
            sthx LADDR
                              ; to LADDR
            ldhx #$EE00
                              ;Load beginning address of the
                              ; row to H:X
            jsr
                  PRGRNGE
                              ;Call PRGRNGE routine
```

The second example shows how to program one full page. The variable CPUSPD is set to a value which reflects an 3 MHz operating frequency, that is $4f_{op} = 4 \times 3 = 12$ (\$0C). However regarding the MC68HLC908QT/QY, PRGRNGE can program a range of FLASH locations that is up to 32 bytes and in the same row. Therefore, these devices can not use this example.

PRGRNGE:	equ	\$2809	;QY4 PRGRNGE jump address
Data load:	ldhx lda	#\$0000 #\$AA	;Index offset into DATA array ;Initial data value (inverted)
	coma sta	DATA, x	;Alternate between \$55 and \$AA ;Fill DATA array, 64 bytes data, ; values to program into FLASH
	aix cphx bne		; (ie. 55, AĀ, 55, AA)
	mov ldhx sthx ldhx		<pre>;fop = 3 MHz in this example ;Load last address of the row ; to LADDR ;Load beginning address of the ; row to H:X</pre>
	jsr	PRGRNGE	;Call PRGRNGE routine



Page Erase Workaround

Regarding the JB8 and JL/JKxx(E) devices, the FLBPR does not consist of FLASH. Therefore, an additional step is required to unlock the FLASH before calling the routine.

9.6 Example for DELNUS

This example shows how to use DELNUS. In this example a 100 μ s delay is generated at $f_{op} = 4$ MHz using the DELNUS delay routine. To use this routine accurately, we need to calculate the value of X and keep track of the delays due to the setup instructions.

First, we need to know how many bus cycles a delay of $100 \ \mu s$ will take. This is simply delay time multiplied by bus frequency.

Bus cycles = $100 \ \mu s \times 4 \ MHz = 400$ cycles.

Next, we determine the value for the accumulator using the relationship:

 $A = CPUSPD = 4 \times f_{op} = 4 \times 4 = 16$ (\$10)

Then we use the relationship:

 $DELNUS = 3 \times (A \text{ value}) \times (X \text{ value}) + 8$

And the fact that we will use 9 bus cycles to setup the routine (lda, ldx, jsr):

DEL_100 μ s = 400 cycles = 9 + DELNUS= 9 + (3 × 16 × X +8)

Solving for X:

 $X = (400 - 17) \div (3 \times 16) = 8$

A = 16 and X = 8 are initialized before calling DELNUS.

DELNUS: equ	\$280C		;QY4	DELNU	S jump	address
DEL_100US:lda	ldx	#\$08		,	X=8	routino
	jsr	DELNUS	;[5]	Call 1	DELNUS	routine

In this example, the total delay time is 9 setup cycles + $(3 \times 16 \times 8 + 8)$ cycles = 401 cycles (100.25 µs).

10 Page Erase Workaround

This section provides a workaround for the page erase operation which described in Section 2, "Page Erase Issue."

To use this workaround, the code in Section 12, "Workaround Code," is programmed in FLASH. It is highly recommended that this routine is placed in an area of FLASH protected by the FLASH block protect register (FLBPR). Before calling this routine, CTRLBYT, CPUSPD, and H:X registers required for the page erase operation using the ERARNGE must be initialized properly. The code executes the following:

1. Copy a part of ERARNGE (page erase step 1 through step 6) located in ROM to RAM. The code is copied to address RAM+\$0A and a total 72 bytes are copied from there.



- Change a loop value to support t_{Erase}=4ms in the code copied to RAM. This change guarantees minimum 10k program/erase FLASH endurance. However for the JB8, this change is not required.
- 3. Replace instruction "STA \$FFFF" with instruction "LDA \$FFFF" in the code copied to RAM. This change avoids writing to \$FFFF due to the COP service.
- 4. Just after the copied routine, add a jump instruction which jumps to page erase step 7 in the original ERARNGE located in ROM.
- 5. Call the routine copied in RAM.

The following example shows how to execute the workaround routine.

```
mov #$10,CPUSPD ;CLEAR BIT 0 DATA DIRECTION
mov #$00,CTRLBYT ;Select page operation
ldhx #$F000
jsr PageErase ;Call a workaround routine
```

Regarding the JB8 and JL/JKxx(E) devices, FLBPR does not consist of FLASH. Therefore, an additional step is required to unlock the FLASH before calling the routine.

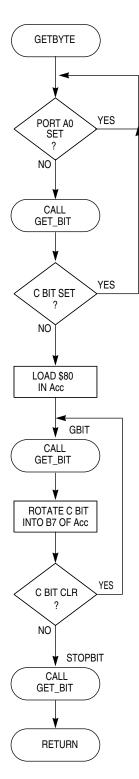
NOTE

COP is not supported in this workaround.

11 ROM Routines Source Code

The following five flowcharts provide graphic explanations of the ROM routines source code.





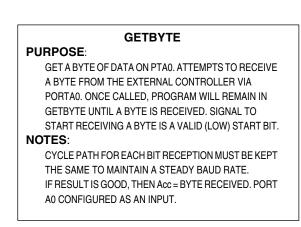


Figure 1. GETBYTE



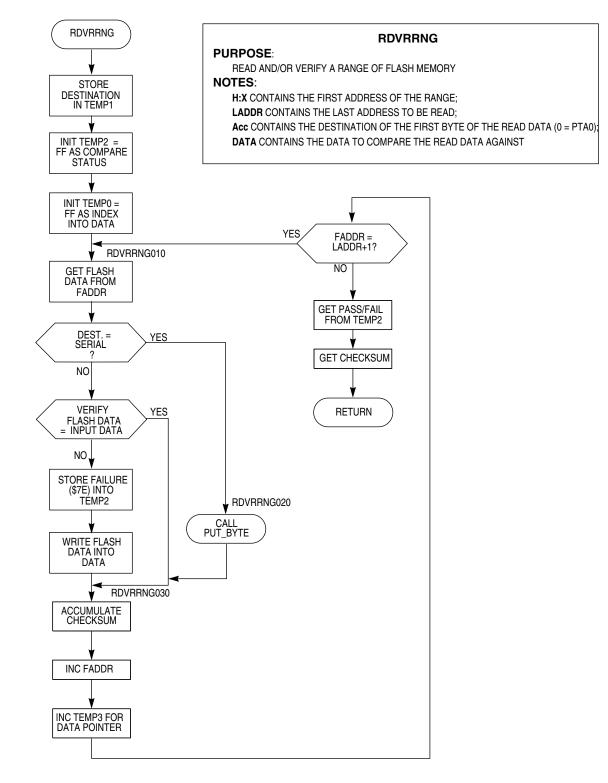


Figure 2. RDVRRNG



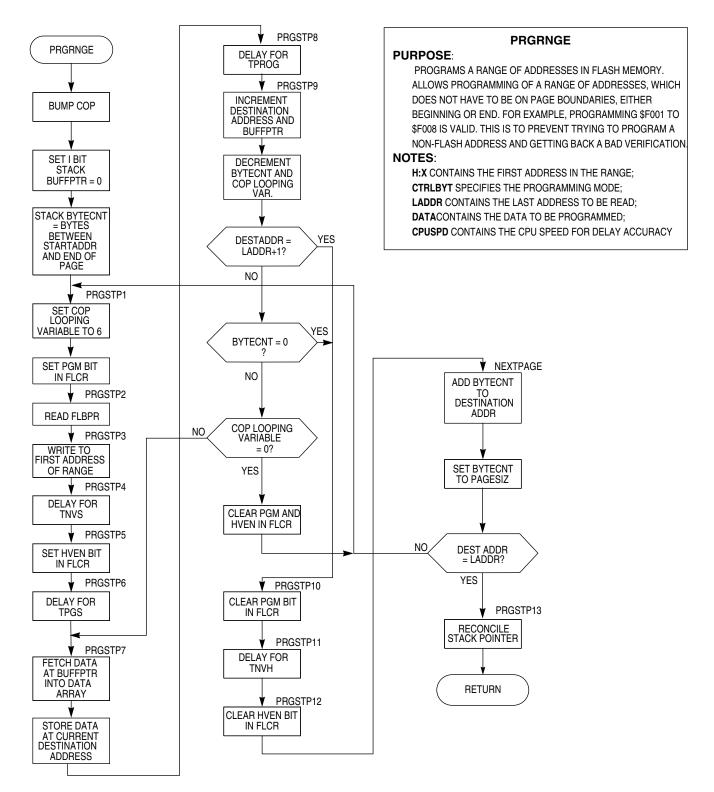
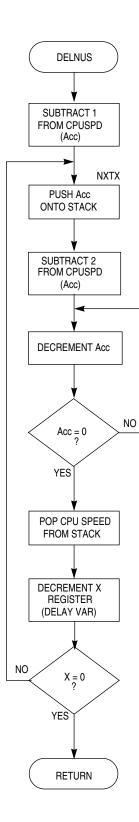


Figure 3. PRGRNGE





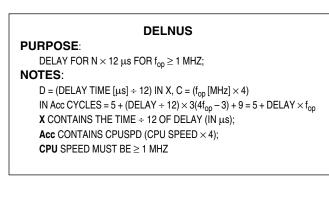
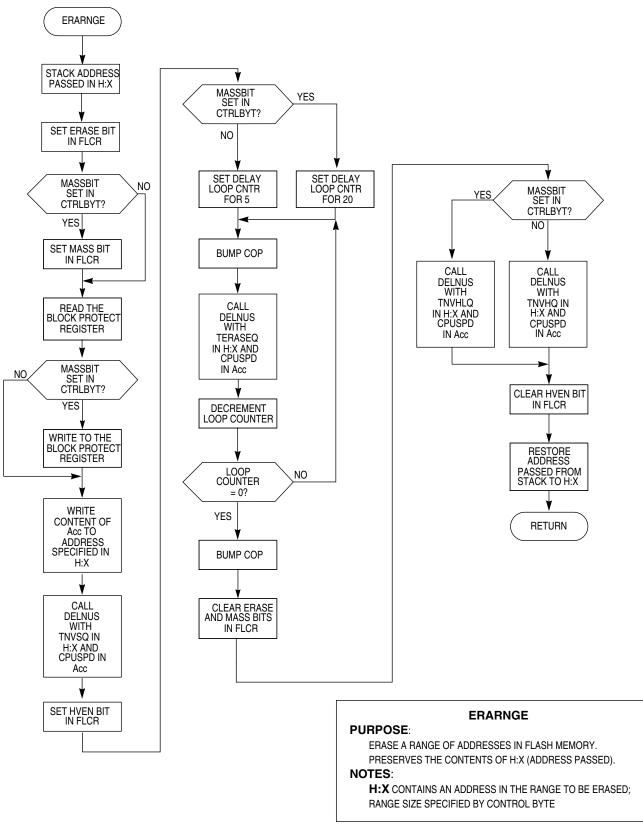


Figure 4. DELNUS









```
* FILE NAME: MAINPR.ASM
 PURPOSE: To provide FLASH erase, program and verify routines
*
        to reside in ROM.
 TARGET DEVICE: MC68HC908GR8, MC68HC908KX8, MC68HC908JL3/JK3 and the MC68HC908JB8
*
 MEMORY USAGE - RAM: 4-36 BYTES, DEPENDING ON DATA PASSED
             ROM: 364 BYTES
*
*
 ASSEMBLER: MCUEZ
*
 VERSION: 1.0.5
*
*
 PROGRAM DESCRIPTION:
* This program contains a structure of routines to facilitate FLASH programming.
* These routines, which are individually callable, are intended to reside in ROM
* for the use of a user program, a test/burn-in program, or for development/programming
tools. This set of routines is included, along with definition files, by the project
 file 9GR8ALLROM.ASM.
* AUTHOR: Grant Whitacre
*
 LOCATION: Austin - Oak Hill, Texas
*
UPDATE HISTORY:
*
 REV
      AUTHOR
                               DESCRIPTION OF CHANGE
                  DATE
 ===
      ================
                  =======
                               _____
 0.0
     G. WHITACRE
                  10/05/98
                               Initial release
 0.1
     G. WHITACRE
                  02/17/99
                               MODIFIED FOR THE SST FLASH
 0.2
     G. WHITACRE
                  08/23/99
                               MODIFIED GETBYTE FOR 9600
                               BAUD @ 2.4576 MHZ
* GENERAL CODING NOTES:
* Bit names are labeled with <port name><bit number> and are used in the commands that
* operate on individual bits, such as BSET and BCLR. A bit name followed by a dot
 indicates a label that will be used to form a bit mask.
* INCLUDED FILES
INCLUDE "E:\MMDS\GR8\SSTROM\H908GR8.FRK"
* EQUATES
* PROGRAMMING TIMES IN us
* FOLLOWING DEFINED IN .FRK FILE
                 40
                                 ;FLASH Byte Program Time
*TPROG
           EQU
                                 ;FLASH Page Erase Time
*TERASE
           EOU
                 1000
                 4000
*TMERASE
           EQU
                                 ;FLASH Mass Erase Time
           EOU
                 10
                                 ;FLASH PGM/ERASE to HVEN Setup Time
*TNVS
*TPGS
           EQU
                 5
                                 ;FLASH Program Hold Time
                 5
                                 ;FLASH High-Voltage Hold Time
*TNVH
           EQU
*TNVHL
           EQU
                 100
                                 ;FLASH High-Voltage Hold Time (Mass Erase)
*TRCV
                 1
                                 ;FLASH Return to Read Time
           EQU
```



* TIMES	S REPRES	SENT VAL	UES THAT ARE PASSED TO) THE DELAY ROUTINE, WHICH
				R TERASE AND TMERASE, THE
* ROUT	INE IS C	ALLED 5	AND 20 (12 µs*17*20=4	080 us) TIMES,
			A BUMP OF THE COP BEFO	•
ECALLS		EQU	5	
MECALLS	z	EQU	20	
TPROGQ		EQU		;FLASH Program Time
TERASE		EQU		;FLASH Block Erase Time
	-	~		;FLASH Mass Erase Time
TMERASI	ΞŲ	EQU		
TNVSQ		EQU		;FLASH PGM/ERASE to HVEN Setup Time
TPGSQ		EQU		;FLASH Program Hold Time
TNVHQ		EQU		;FLASH High-Voltage Hold Time
TNVHLQ		EQU		;FLASH High-Voltage Hold Time (Mass Erase)
TRCVQ		EQU	1	;FLASH Return to Read Time
* * * * * * *	* * * * * * * *	******	* * * * * * * * * * * * * * * * * * * *	*******
* ROUT				
*****	******	******	* * * * * * * * * * * * * * * * * * * *	***************************************
*****	* * * * * * * *	******	* * * * * * * * * * * * * * * * * * * *	***************
* NAME:	GETBYTE	2		
* PURPC	SE: Get	a byte c	of data on PTAO	
* Entry	Condit:	ions: Po	rt A0 configured as an	input.
* Exit	Conditi	ons: A	cc=byte received.	
*		I	f break received or re	esult bad then send break and
*		jump b	ack to start.	
*		Port	A0 configured as an inp	out.
* SUBRC	UTINES (CALLED: (
	BLES REA			
	BLES MOI			
	USED: 4			
	20 BYTE			
			D OUT OF ROM	
				mal controller via PortA0.
				TE until a byte is received
-			eiving a byte is a val	
			r each bit reception m	nust be kept the same to maintain
	eady bau			
			23) = 256 CYCLES @ 2.4576 N	
*****	* * * * * * * *	******	* * * * * * * * * * * * * * * * * * * *	***************************************
GETBYTI				
	BRSET0	,PTA,GE	TBYTE	;Waiting for start edge.
	JSR	GET_BII	ר -	;try to receive a full start bit.
	BCS	GETBYTE	E	;Success?
	LDA	#\$80		; initialize receiver.
GBIT:				;got start bit, now get byte.
	JSR	GET_BII	1	;5
	RORA			;1 bit into Acc
	BCC	GBIT		;3 get next bit
*				; baud calculation
STOPBI	Г:			,
	JSR	GET_BII	1	;look for stop bit
	RTS	JUI _ UI I		, took for beep bit
******		******	* * * * * * * * * * * * * * * * * * * *	******



```
ROM Routines Source Code
```

* NAME: RDVRRNG PURPOSE: Read and/or Verify a range of FLASH memory ENTRY CONDITIONS: H:X contains the first address of the range; LADDR contain the last address to be read; Acc contains a Boolean to see if read data * goes to PTA0 (0=PTA0, else Data Array) DATA contains the data to compare the read data against * EXIT CONDITIONS: C bit is set if good compare; Acc contains checksum; DATA contains read FLASH data * SUBROUTINES CALLED: * VARIABLES READ: LADDR, DATA ARRAY * VARIABLES MODIFIED: DATA ARRAY * STACK USED: 6 * SIZE: 63 BYTES * DESCRIPTION: EXECUTED OUT OF ROM; ALTHOUGH THIS ROUTINE SERVICES THE COP, * THERE COULD STILL BE A COP TIME OUT UNDER CERTAIN CONDITIONS. THESE CONDITIONS * ARE: 1) IN USER MODE, 2) COP ENABLED, 3) USING THE SHORT COP TIMEOUT, 4) NOT USING * THE PLL SUCH THAT f_{OP} = CGMXCLK/4 RDVRRNG: PSHA ; (A) SAVE DESTINATION FLAG ON STACK AS 4, SP ;LOCAL VARIABLE FOR CHECKSUM STARTS AT 00 CLRA PSHA ; (B) SAVE ON STACK AS 3, SP ;LOCAL VARIABL FOR INDEX INTO DATA STARTS AT 00 PSHA ; (C) SAVE ON STACK AS 2, SP COMA ;LOCAL VARIABLE FOR VERIFY STATUS (FF = GOOD) PSHA ; (D) SAVE ON STACK AS 1, SP RDVRRNG010: STA ; BUMP THE COP \$FFFF LDA , X ; LOAD CONTENT OF FLASH ADDRESS INTO ACC. TST 4,SP ;CHECK DESTINATION FLAG BEO RDVRRNG020 ;SKIP COMPARE IF DESTINATION IS PTA0 ; (E) STORE FADDR FOR LATER PSHX PSHH ; (F) LDX 4,SP ;GET INDEX INTO DATA FROM STACK CLRH CMP DATA,X ; COMPARE ADDR NOW IN X SO COMPARE CONTENT RDVRRNG015 ; IF EQUAL THEN KEEP GOING ... BEQ STA DATA,X ;WRITE FLASH DATA THAT IS DIFFERENT TO RAM LDX #\$7E ;FAILED VERIFICATION SO CLEAR VERIFY STATUS 3,SP ; MUST KEEP DATA IN ACC FOR CHECKSUM BELOW STX RDVRRNG015: ; (F')GET FADDR BACK PULH ;(E') PULX BRA RDVRRNG030 ;NOT COMPARING, JUST DUMPING RDVRRNG020: JSR ;WRITE DATA TO PORT A0... PUT_BYTE ; PUT_BYTE SAVES A, X, AND H RDVRRNG030: ADD 3,SP ; ADD VALUE OF CURRENT BYTE TO CHECKSUM STA 3,SP ; MAINTAIN AS RUNNING SUM INC 2,SP ; INCREMENT INDEX INTO DATA



CPHX LADDR ; COMPARE SOURCE ADDR TO THE LAST ADDRESS BHS NOMO ; IF NOT YET DONE, LOOP FOR ANOTHER ; INCREMENT SOURCE ADDRESS AIX #1 RDVRRNG010 BRA NOMO PULA ; (D')GET PASS/FAIL INFO INTO ͲϪΡ ; CARRY BIT PULA ; (C') TRASH INDEX INTO DATA PULA ; (B')RETURN CHECKSUM IN ACC. AIS #1 ; (A') TRASH DESTINATION FLAG RTS * NAME: PRGRNGE * PURPOSE: Programs a range of addresses in FLASH memory ENTRY CONDITIONS: H:X contains THE FIRST address in the range; CTRLBYT contains the Control Byte that specifies * the programming mode; LADDR contains the last address to be read; DATA contains the data to be programmed * EXIT CONDITIONS: Next address in H:X * SUBROUTINES CALLED: DELNUS * VARIABLES READ: CONTROL BYTE, CPUSPD, LADDR, DATA ARRAY * VARIABLES MODIFIED: * SIZE: 170 BYTES * STACK SIZE (INCLUDING CALL): 7 BYTES * DESCRIPTION: EXECUTED OUT OF ROM * Allows passing of a range of addresses to PRGRNGE, which does not have * to be on row boundaries, either beginning or end. I.e., passing \$F001 to * \$F008 is valid. This is to prevent trying to program a non-FLASH address. ***** PRGRNGE: SEI ; MASK INTERRUPTS SO THAT DELAYS ARE NOT ; AFFECTED CLRA ;STORES INDEX INTO DATA ARRAY PSHA ; (A) INDEX INTO DATA IS ON STACK PSHX ; (B) SAVE FADDR SO THAT IT IS NOT DESTROYED PSHH ; (C) ;GET (FADDR MODULUS ROWSIZE) ТХА LDX #ROWSIZ ;HIGH BYTE CAN BE IGNORED BECAUSE ROWSIZE CLRH ; IS ALWAYS A POWER OF TWO AND 256 OR LESS. ; IT MUST BE IGNORED SO THAT RESULT OF DIVIDE ; WILL FIT IN ONE BYTE. ; DIVIDE LEAVES REMAINDER (MODULUS) IN H DIV PSHH ; (D) PUSH REMAINDER IN H ONTO STACK TXA ; MOVE ROWSIZE TO ACC SUB 1,SP ;SUBTRACT REMAINDER TO GET #BYTES TO PROGRAM ; (D') PULL REMAINDER FROM STACK AND THROW AWAY PULH ; (C')GET FADDR BACK FROM STACK PULH PULX ; (B') ; (B) STORE #BYTES TO END OF ROW ON STACK PSHA PSHA ; (C) RESERVE A STACK LOC. FOR COP LOOPING VAR. ;3,SP = COP LOOPING VARIABLE ;4,SP = #BYTES TO END OF ROW

		;5,SP = INDEX INTO DATA ARRAY
PRGSTP1:		
STA	\$FFFF	; BUMP COP
LDA STA		;SET LOOPING VARIABLE TO ALLOW FOR COP BUMP; ;NEED TO TURN OFF PGM AND HVEN OCCASIONALLY TO
SIA	1,SP	; BUMP COP
LDA	#PGM.	;SET PGM BIT
ORA	FLCR	
AND	#\$F9	;(\$FF-MERASEERASE.)
6 7 73		;MAKE SURE ERASE BITS ARE OFF
STA	FLCR	;WRITE THIS TO THE FLASH CONTROL REG.
PRGSTP2 LDA	FLBPR	;READ FROM BLOCK PROT. REG.
PRGSTP3:		
IFEQ	TESTMOD	
LDA	, X	
ENDIF		
IFNE STA	TESTMOD ,X	;WRITE TO ANY FLASH ADDRESS WITHIN THE ROW
ENDIF	•	, WATTE TO ANT FLASH ADDRESS WITHIN THE ROW
		; TO BE PROGRAMMED WITH ANY DATA
PSHH		; (D)
PSHX		;(E)
PRGSTP4 LDX	#TNVSQ	; DELAY FOR TNVS
LDA	CPUSPD	
BSR	DELNUS	
PRGSTP5 LDHX	#FLCR	;SET THE HVEN BIT IN FLCR
	, X	
ORA	#HVEN.	
STA	, X	
PRGSTP6 LDX	#TPGSQ	;DELAY FOR TIME TPGS
LDA	CPUSPD	
BSR	DELNUS	
PULX		;(E')
PULH		; (D'
	* * * * * * * * * * * * * * * * * * * *	****
* 6 BYTES, TI	HEN REPEAT PROCESS UNTIL H	
	* * * * * * * * * * * * * * * * * * * *	***************************************
PRGSTP7 PSHH PSHX		; (D) ; (E)
FSIIX		(L); 1, SP = ADDR(LSB)
		;2, SP = ADDR(MSB)
		;3,SP = COP LOOPING VARIABLE
		;4,SP = #BYTES TO END OF ROW
		; 5, SP = INDEX INTO DATA ARRAY
CLRH LDX	5,SP	;GET 0:BUFFPTR INTO H:X ;GET THE INDEX INTO DATA ARRAY
LDA	DATA,X	;GEI THE INDEX INTO DATA ARRAY ;LOAD BYTE TO PROG FROM DATA+BUFFPTR
1 1 2 1 2 1 2 1 2 1 2 2 2 2 2 2 2 2 2 2	,	, 2012 212 10 1100 INON DATH DOTTIN

Using MC68HC908 On-Chip FLASH Programming Routines, Rev. 3

NP



ROM Routines So	ource Code	
PULX		;(E') POP LO BYTE OF ADDR BACK INTO X
PULH		;(D')
IFEQ TEST	IMOD	
LDA	, X	
ENDIF		
IFNE TEST	TMOD	
STA	, X	;STORE DATA TO ADDR SPEC.BY H-X
ENDIF		
PSHH		; (D)
PSHX		;(E)
PRGSTP8 LDX		; DELAY FOR TPROG
LDA		
BSR	DELNUS	
PULX		;(E')
PULH		;(D')
PRGSTP9:		
AIX	#\$01	; INCREMENT THE DESTINATION ADDRESS
INC	3,SP	; INCREMENT THE POINTER INTO DATA
DEC	2,SP	; DECREMENT THE BYTE COUNTER
DEC	1,SP	; DECREMENT COP LOOPING VARIABLE
CPHX	LADDR	; CHECK FOR END OF RANGE
BHI	PRGSTP10	;EXIT LOOP IF PAST END OF RANGE
TST	2,SP	;CHECK FOR END OF ROW
BEQ	PRGSTP10	;EXIT LOOP IF DONE WITH ROW
TST	1,SP	
BNE	PRGSTP7	; COP VAR = 0 ?
BSR	CLR_P_H	;
TAX		
BRA	PRGSTP1	;
PRGSTP10:		
BSR	CLR P H	;CALL RTN TO CLEAR PGM AND HVEN
NEXTROW:		; DONE WITH ROW, GET READY TO EXIT
NEXTION.		;1,SP = COP LOOPING VARIABLE
		;2,SP = #BYTES TO END OF ROW
		;3,SP = INDEX INTO DATA ARRAY
ADD	2,SP	; ADD BYTES PROGRAMMED TO LOW BYTE
TAX	2,51	, ADD BITES FROMAEND TO DOW DITE
PSHH		;(D) CORRECT HIGH BYTE FOR CARRY, IF ANY
PULA		; (D') CORRECT HIGH BITE FOR CARRY, IF ANT
ADC	#0	, (D)
PSHA	#0	; (D)
PULH		; (D')
LDA	#ROWSIZ	;
STA	2,SP	; #BYTES TO END OF ROW IS ROWSIZE
AIX	#-1	; DECREMENT CURRENT ADDRESS BY 1 TO COMP.
		; TO LAST ADDR
CPHX	LADDR	;COMPARE FADDR TO LADDR
AIX	#1	
BLO	PRGSTP1	; PROGRAM ANOTHER ROW IF LESS OR EQUAL



PRGSTP13: ;NEXT 3 INST. TAKE > 1 μs . ; (C') REMOVE COP LOOP VARIABLE PULA ; (B')REMOVE #BYTES TO END OF ROW PULA PULA ; (A') REMOVE INDEX INTO DATA ADDRESS DONEPRG RTS * FOLLOWING LOCAL SUB-ROUTINE CLEARS PGM, DELAYS, THEN CLEARS HVEN. CLR_P_H PSHH ;(D) PSHX ;(E) LDHX #FLCR ;CLEAR PGM BIT LDA , X **#PGM**. EOR STA , X PRGSTP11: LDX #TNVHQ ; DELAY FOR TNVH LDA CPUSPD DELNUS BSR PRGSTP12: #FLCR ;CLEAR THE HVEN BIT LDHX LDA , X EOR #HVEN. STA , X ;(E') PULA PULH ; (D') RTS ***** * NAME: DELNUS * PURPOSE: Delay N ms * ENTRY CONDITIONS: X CONTAINS THE TIME/12 OF DELAY (IN ms). A CONTAINS THE CPU SPEED X 4 (2 BITS OF PRECISION) * EXIT CONDITIONS: * SUBROUTINES CALLED: * VARIABLES READ: * VARIABLES MODIFIED: * SIZE: 10 BYTES * STACK USED (INCLUDING CALL): 3 BYTES * DESCRIPTION: EXECUTED OUT OF ROM * Delay Routine for $f_{\rm OP}$ >= 1 MHz, Delay >= 12 ms * (delay time[μ s]/12) in H:X, (f_{OP}[MHz]*4) in Acc * If $f_{OP} > 1$ then * CYCLES = 5+Delay/12[3($4f_{OP}$ -3)+9] = 5+DELAY* f_{OP} * If $f_{OP} = 1$ then CYCLES = 5+12(DELAY/12) = 5+DELAY * where delay in μs and f_{OP} in MHz ;1 CYCLE DELNUS: DECA NXTX PSHA ;2 DECA ;1 DECA ;1 ;3 DBNZA PULA ;2



DBNZX NXTX ;3 RTS ;4 **** ***** * NAME: ERARNGE PURPOSE: Erase a range of addresses in FLASH memory ENTRY CONDITIONS: H-X contains an address in the range to be erased; range size specified by Control Byte * If b6 = 1 then mass erase, otherwise erase * 1 page (64 bytes for the GR8). EXIT CONDITIONS: Preserves the contents of H:X (address passed) * * SUBROUTINES CALLED: DELNUS * VARIABLES READ: CTRLBYT, CPUSPD * VARIABLES MODIFIED: STACK USED: 5 * SIZE: 99 BYTES DESCRIPTION: Does not check for a blank range before (to see if erase is necessary) or after (to see if successful erase) ***** ERARNGE: SEI PSHH ;KEEP ADDRESS PASSED PSHX CLRA ;SET ERASE BIT, AND ORA #ERASE. BRCLR MASSBIT, CTRLBYT, AMBS #MASS. ; MASS BIT IF NECESSARY ORA AMBS: STA FLCR ERABLK LDA FLBPR ; READ THE BLOCK PROTECT REGISTER IFEQ TESTMOD ;WRITE TO ANY ADDRESS IN ERASE RANGE LDA FLBPR LDA , X ENDIF IFNE TESTMOD BRCLR MASSBIT, CTRLBYT, NOBLWR STA FLBPR NOBLWR STA , X ENDIF LDX #TNVSQ ; DELAY FOR TNVS CPUSPD LDA BSR DELNUS #FLCR LDHX ;SET THE HVEN BIT IN FLCR LDA , X ORA #HVEN. STA , X MASSBIT, CTRLBYT, RWERASE BRCLR LDA #MECALLS ; DELAY LOOPS FOR TMERASE BRA ERADEL OR ; RWERASE LDA #ECALLS ; DELAY LOOPS FOR TERASE

```
Workaround Code
```

NP_	_		
			Worka
ERADEL	PSHA		;STACK INCREMENT COUNTER
BUMPCOI	P STA	\$FFFF	;BUMP COP
	LDX	#TERASEQ	;SAME FOR TERASEQ AND TMERASEQ
	LDA	CPUSPD	
	BSR	DELNUS	
	DEC	1,SP	
	BNE	BUMPCOP	
	PULA		; PULL INCREMENT CNTR OFF STACK
	STA	\$FFFF	; BUMP COP WHEN DONE DELAYING
	LDHX	#FLCR	;CLEAR THE ERASE BIT
	LDA	, X	
	EOR	#ERASE.	
	AND	#(\$FF-MASS.)	;CLEAR MASS BIT
	STA	, X	
	BRCLR	MASSBIT, CTRLBYT, PGSTUP	
	LDHX	#TNVHLQ	;DELAY FOR TNVHL
	BRA	STUPDEL	; OR
PGSTUP	LDHX	#TNVHQ	;DELAY FOR TNVH

```
S BIT
                                        TNVHL
                                        TNVH
STUPDEL LDA
          CPUSPD
     BSR
          DELNUS
          #FLCR
     LDHX
                                ;CLEAR THE HVEN BIT
     LDA
          , X
     EOR
          #HVEN.
     STA
          ,Х
XERARNG PULX
                                ;RESTORE ADDRESS PASSED
     PULH
                                ;THESE 3 INST. DELAY FOR
                                ;AT LEAST 1 µs (TRCV)
     RTS
```

Workaround Code 12

```
;********
;* NAME: PageErase
;* Assembler: P&E Microcomputer Systems Casm08
;* PURPOSE:
;* This routine is used for erasing a page size of FLASH.
;* In this routine, a part of ERARNGE routine located in ROM is
;*
  copied into RAM and then execute the routine out of RAM.
   To work a page erase operation properly, set proper values at
;*
;* Setup 1 - 4.
;* ENTRY CONDITIONS:
    H:X contains an FLASH address whithin a page to be erased
;*
;*
   Bit 6 in CTRLBYT is cleared
;*
   CPUSPD contains an integer of 4 x bus frequency [MHz]
;*
  COP must be disabled
;* EXIT CONDITIONS:
```

Workaround Code

```
;*
   I bit is set
;*
   The contents of H:X (address passed) is preserved
;* SUBROUTINES CALLED: DELNUS
;* VARIABLES READ: CTRLBYT, CPUSPD
;* STACK USED: 10 bytes (including the call to this routine)
;* SIZE OF THIS CODE:
   908GR4/8, 908KX2/8, 908JK1(E), 908JL/JK3(E) - 33 bytes
;*
;*
   908JB8 - 29 bytes
;* Note:
 a. Locations from RamStart+$0A to RamStart+$54 is used in this
;*
;*
    routine, where RamStart is a start address of RAM.
;* b. Since the COP is not supported, it must be disabled.
Setup 1: Device Selection
;*
   Distinguish between HC908JB8 and other parts
;*
$SETNOT
       JB8
                    ;This example does not select JB8
;* $SET
          JB8
                    ;Use this setup if a part is JB8
;*
  Setup 2: FLASH start address (locFLASH)
   Specify a start address where this routine is placed in FLASH.
;*
;*
   We highly recommend that this routine is protected by FLBPR.
locFLASH:
            $FDC0
       equ
Setup 3: RAM start address (RamStart)
;*
;*
   For 908GR4/8, 908KX2/8, 908JB8
;*
    RamStart: equ $0040
;*
   For 908JK1(E), 908JL/JK3(E)
           equ $0080
;*
     RamStart
$0040
                    ; This example for the HC908GR8
RamStart: equ
;*
  Setup 4: DELNUS start address (DELNUS)
;*
   For 908GR4/8
;*
     DELNUS:
             equ
                 $1D96
;*
  For 908KX2/8
;*
     DELNUS:
            equ
                 $12C3
;*
   For 908JK1(E), 908JL/JK3(E), 908JB8
;*
     DELNUS:
             equ
                 $FD21
$1D96
                    ;This example for the HC908GR8
DELNUS:
        equ
DATSTRC:
            RamStart+8 ;data array starts from RamStart
        equ
CodeSize:
            $48
                   ;72 byte code to be copied to RAM
        equ
;* Variable locations used in this routine.
        org
            DATSTRC
```



CTRLBYT:	rmb	1	;control byte for erase size
CPUSPD:	rmb	1	;CPU speed
codeRAM:	rmb	CodeSize	;a part of the ERARNGE is copied to ; this location.
CodeJmp:	rmb	3	;jump to ROM routine
ramERARNGE:	equ	codeRAM+\$A	;ERARNGE start address in RAM
locECALLS:	equ	codeRAM+\$37	;location where ECALLS is initialized
locCOP:	equ	codeRAM+\$39	;location where COP is serviced
jmpAddr:	equ	DELNUS+\$4B	;jump location to a part of the ERARN
ECALLS:	equ	\$14	;support 4ms Terase
exLDA:	equ	\$C6	;extended LDA instruction
exJMP:	equ	\$CC	;extended JMP instruction
	org	locflash	
PageErase:			
	pshx		;save H and X values to stack
	pshh		
	ldhx	#CodeSize	;initialize pointer
Code2RAM:			
	lda	DELNUS-1,x	;copy DELNUS and a part of ERARNGE
	sta	codeRAM-1,x	
	dbnzx	Code2RAM	;decrement pointer and loop back
			; until done
\$IFNOT JB8			;if JB8 is selected in Setup 1, two
			; instructions below are not included
	lda	#ECALLS	;change 1ms to 4ms for Terase
	sta	locecalls	
\$ENDIF			
	lda	#exLDA	;change "sta \$FFFF" to "lda \$FFFF"
	sta	locCOP	; in ERARNGE
	mov	<pre>#exJMP,CodeJ</pre>	Jmp
			;add "jmp ROM_step7" just after copie
	ldhx	#jmpAddr	; code
	sthx	CodeJmp+1	
	pulh		;set a location within a page to be
	pulx		; erased at H:X
	jsr	ramERARNGE	; execute a page erase operation from
	rts		, sitte a bage stabe operation from

NP



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